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APPROVAL SHEET

Part No:

BF3A03G-NPD

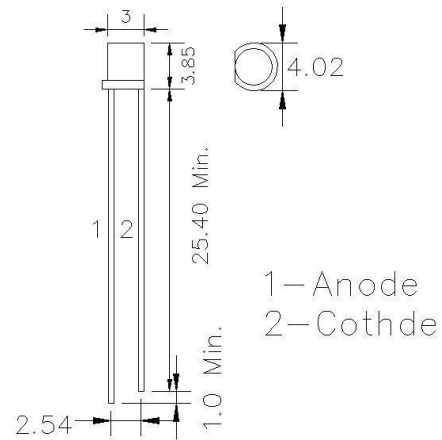
NOTE : Green Part

MAKER			CUSTOMER	
				
R&D	QA	Sales	Checked	Approved
				

Prepared	Checked	Approved
Rachel Lee	Sky Lin	Kenneth Wu

DESCRIPTION:

Device Type : BF3A03G-NPD
 Dice Material : Silicon
 Lens Color : Water Clear
 Lens Dimension : 3 mm



Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Rating.	Unit
Reverse Voltage	V _R	30	V
Power Dissipation	P _C	100	mW
Operating Temperature	T _{opr}	-30 ~ +80	°C
Storage Temperature	T _{str}	-30 ~ +100	°C
Solder DIP (MAX. 5 seconds, 1.6mm from body) Temperature 260°C			

Electrical and Optical Characteristics at Ta=25°C

Description	Symbol	Condition	Min.	Typ.	Max.	Unit
Range of Spectral Bandwidth	W _p		400		1100	nm
Peak sensitive wavelength	W _p			940		nm
Reverse Light Current	I _L	V _R =5V.Ee=1mW/ cm ²		10		uA
Reverse Dark Current	I _D	V _R =10V.Ee=0mW/ cm ²		-	10	nA
Reverse breakdown voltage	V _{BR}	I _R =100uA.Ee=0mW/ cm ²	30			V
Open-Circuit Voltage	V _{OC}	Ee=5mW/cm ² λ _p =940nm		0.35		V
Short- Circuit Current	I _{sc}	Ee=1mW/cm ² λ _p =940nm		40		μA
Rise Time/ Fall Time	t _r / t _f	V _R =10V R _L =1KΩ		45 / 45		ns
Total Capacitance	C _t	V _R =5V Ee=0mW/cm ² f=1MHz		15		pF

- Note:
- 1.The lead should be formed up to 5mm from the body of device without forming stress.
 2. Soldering shall be performed after lead forming.
 3. All dimensions are in millimeters

LED LAMP Technical Data

Typical Optical-Electrical Characteristic Curves

